

IN THE CLAIMS:

>Please amend claim 56 as follows:

56. (Amended) An apparatus for processing a semiconductor provided on a substrate comprising:

a vacuum chamber;

an ion introducing apparatus connected to said vacuum chamber for doping a semiconductor layer formed on a substantially square substrate with a dopant impurity;

a laser processing apparatus connected to said ion introducing apparatus through said vacuum chamber for treating said semiconductor layer with a laser light after said doping; and

a mechanism provided to said vacuum chamber for transporting said substantially square substrate from said ion introducing apparatus to said laser processing apparatus without exposing said substantially square substrate to the air,

said laser processing apparatus comprising a chamber and a laser wherein a rectangular-shaped laser beam having an elongated cross-section irradiates said non-single crystal silicon film and wherein said rectangular-shaped laser has a [width] length greater than a width of said substantially square substrate.

Please add new claim 74 as follows:

-- 74. An apparatus for processing a semiconductor provided on a substrate comprising: